

# Significant Improvement of Semiconducting Performance of the Diketopyrrolopyrrole-Quaterthiophene Conjugated Polymer through Side-Chain Engineering via Hydrogen-Bonding

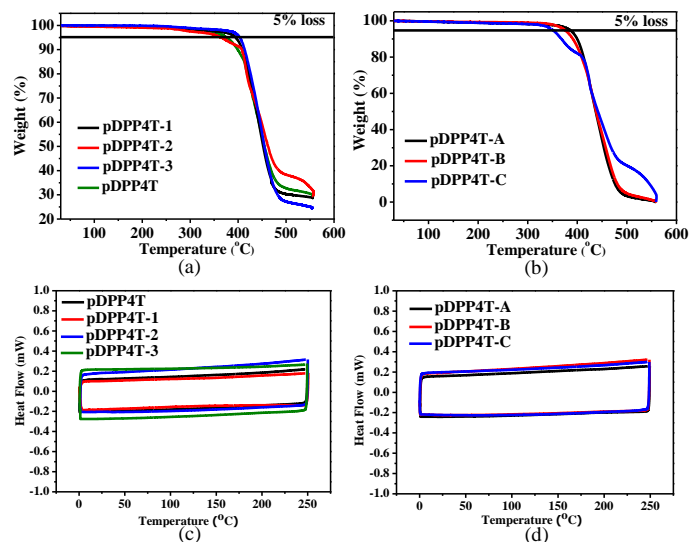
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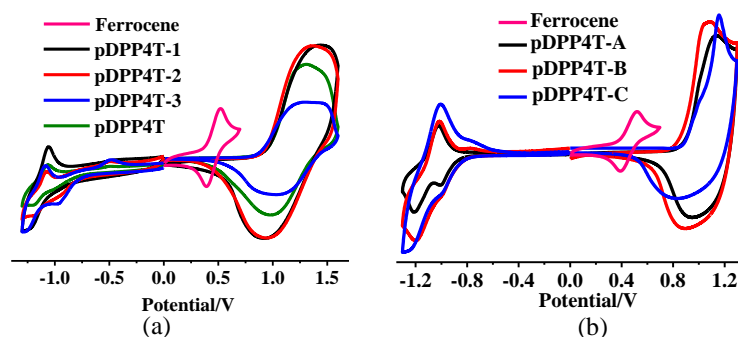
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## 1. Thermogravimetric Analysis (TGA) and Differential Scanning Calorimetry (DSC) Curves



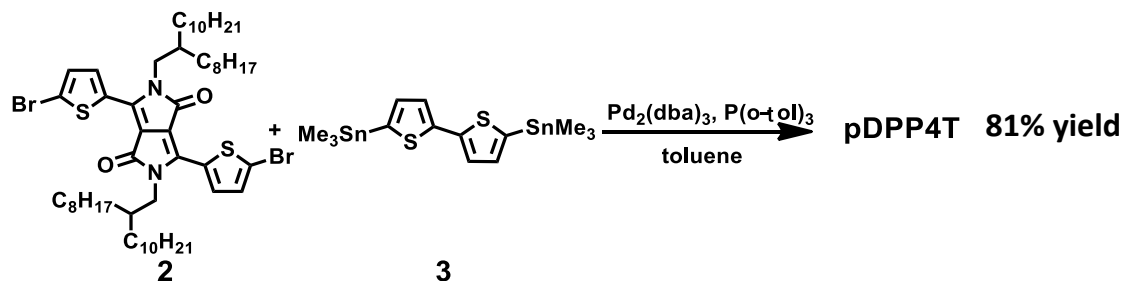
**Figure S1.** (a-b) TGA curves of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C**: heating rate: 10 °C/min. From 25 °C to 550 °C under nitrogen atmosphere; (c-d) DSC curves (endo up) of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** recorded at a heating and cooling rate (0-250 °C) of 10 °C/min under nitrogen.

## 2. Cyclic Voltammograms

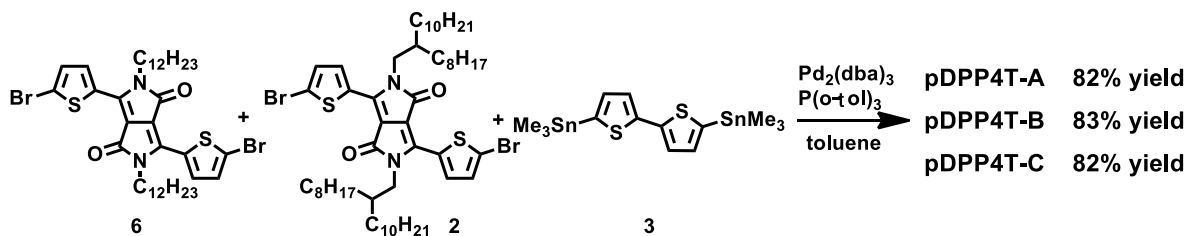


**Figure S2.** Cyclic voltammograms of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** films at a scan rate of 100 mVs<sup>-1</sup>. Pt was used as working electrode and counter electrode and Ag/AgCl (saturated KCl) as reference electrode; *n*-Bu<sub>4</sub>NPF<sub>6</sub> (0.1 M) in CH<sub>3</sub>CN as supporting electrolyte. For calibration, the redox potential of ferrocene/ferrocenium (Fc/Fc<sup>+</sup>) was measured under the same conditions.

### 3. Synthesis and Characterization of pDPP4T, pDPP4T-A, pDPP4T-B and pDPP4T-C



**Synthesis of pDPP4T.** Compound **2** (101.9 mg, 0.10 mmol), compound **3** (49.2 mg, 0.10 mmol),  $\text{P}(\text{o-tol})_3$  (4.9 mg, 0.016 mmol) and  $\text{Pd}_2(\text{dba})_3$  (1.8 mg, 0.0020 mmol) were used. The purified polymer was collected to give deep green solid (83.3 mg, 81% yield).  $^1\text{H}$  NMR (500 MHz, 1,1,2,2-tetrachloroethane- $d_2$ , 100 °C):  $\delta$  8.98-8.92 (m, br, 2H), 7.31-6.94 (m, br, 6H), 4.09-4.02 (m, br, 4H), 2.18-2.03 (m, br, 10H), 1.30 (s, 56H), 0.92 (s, 12H);  $^{13}\text{C}$  NMR (100 MHz, solid):  $\delta$  160.09, 140.33, 136.05, 128.04, 123.69, 107.94, 45.24, 38.36, 32.08, 30.09, 23.05, 14.41;  $M_w/M_n$  (GPC) = 40.2/18.8 kg mol $^{-1}$ . Anal. calcd for  $(\text{C}_{62}\text{H}_{90}\text{N}_2\text{O}_2\text{S}_4)_n$ : C, 72.75; H, 8.86; N, 2.74; S, 12.53. Found: C, 72.50; H, 8.92; N, 2.78; S, 12.39.



**Synthesis of pDPP4T-A.** Compound **6** (2.6 mg, 0.0033 mmol), compound **2** (101.9 mg, 0.10 mmol), compound **3** (50.7 mg, 0.10 mmol),  $\text{P}(\text{o-tol})_3$  (5.0 mg, 0.016 mmol) and  $\text{Pd}_2(\text{dba})_3$  (1.9 mg, 0.0021 mmol) were used. The purified polymer was collected to give deep green solid (86.7 mg, 82% yield).  $^1\text{H}$  NMR (500 MHz, 1,1,2,2-tetrachloroethane- $d_2$ , 100 °C):  $\delta$  8.85 (s, br, 2H), 7.07-6.91 (m, br, 6H), 4.09 (s, br, 4H), 2.25-2.08 (m, br, 10H),

1.67-1.32 (m, br, 56H), 0.93 (s, 12H);  $^{13}\text{C}$  NMR (100 MHz, solid):  $\delta$  160.91, 140.94, 137.32, 129.00, 124.76, 108.64, 45.08, 38.79, 37.63, 32.66, 30.58, 23.56, 14.88.  $M_w/M_n$  (GPC) = 211.6/74.0 kg mol $^{-1}$ . Anal. calcd. for  $(\text{C}_{1936}\text{H}_{2878}\text{N}_{62}\text{O}_{62}\text{S}_{124})_n$ : C, 72.69; H, 9.07; N, 2.71; S, 12.43. Found: C, 72.27; H, 8.57; N, 2.82; S, 12.51.

**Synthesis of pDPP4T-B.** Compound **6** (4.0 mg, 0.0050 mmol), compound **2** (101.9 mg, 0.10 mmol), compound **3** (51.8 mg, 0.11 mmol),  $\text{P}(o\text{-tol})_3$  (5.1 mg, 0.017 mmol) and  $\text{Pd}_2(\text{dba})_3$  (1.9 mg, 0.0021 mmol) were used. The purified polymer was collected to give deep green solid (88.7 mg, 83% yield).  $^1\text{H}$  NMR (500 MHz, 1,1,2,2-tetrachloroethane- $d_2$ , 100  $^\circ\text{C}$ ):  $\delta$  8.89 (s, br, 2H), 7.08-6.93 (m, br, 6H), 4.09 (s, br, 4H), 2.25-2.07 (m, br, 10H), 1.69-1.32 (m, br, 56H), 0.93 (s, 12H);  $^{13}\text{C}$  NMR (100 MHz, solid):  $\delta$  160.87, 141.25, 136.74, 128.59, 124.29, 108.37, 45.46, 38.73, 32.67, 30.72, 23.62, 14.94.  $M_w/M_n$  (GPC) = 190.9/91.5 kg mol $^{-1}$ . Anal. calcd. for  $(\text{C}_{1306}\text{H}_{1938}\text{N}_{42}\text{O}_{42}\text{S}_{84})_n$ : C, 72.64; H, 9.05; N, 2.72; S, 12.47. Found: C, 71.89; H, 8.68; N, 2.80; S, 12.49.

**Synthesis of pDPP4T-C.** Compound **6** (8.0 mg, 0.010 mmol), compound **2** (101.9 mg, 0.10 mmol), compound **3** (54.1 mg, 0.11 mmol),  $\text{P}(o\text{-tol})_3$  (5.4 mg, 0.018 mmol) and  $\text{Pd}_2(\text{dba})_3$  (2.0 mg, 0.0022 mmol) were used. The purified polymer was collected to give deep green solid (92.2 mg, 82% yield).  $^1\text{H}$  NMR (500 MHz, 1,1,2,2-tetrachloroethane- $d_2$ , 100  $^\circ\text{C}$ ):  $\delta$  8.99-8.90 (m, br, 2H), 7.14-6.97 (m, br, 6H), 4.11-4.00 (s, br, 4H), 2.10-2.06 (m, br, 10H), 1.47-1.33 (m, br, 56H), 0.92 (s, 12H);  $^{13}\text{C}$  NMR (100 MHz, solid):  $\delta$  160.21, 140.49, 136.35, 128.20, 123.69, 108.09, 45.09, 38.55, 31.93, 30.14, 23.05, 14.39.  $M_w/M_n$

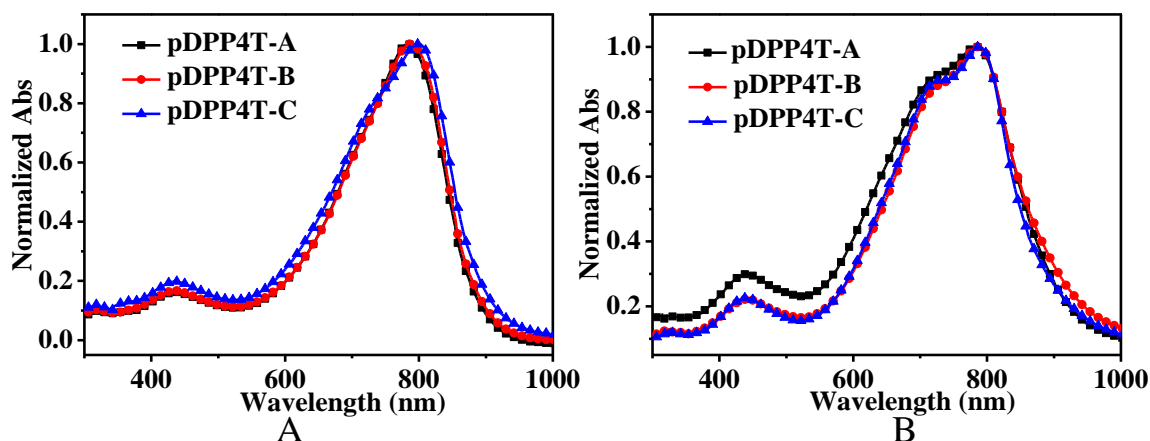
(GPC) = 207.8/94.6 kg mol<sup>-1</sup>. Anal. calcd. for (C<sub>666</sub>H<sub>958</sub>N<sub>22</sub>O<sub>22</sub>S<sub>44</sub>)<sub>n</sub>: C, 72.48; H, 8.75; N, 2.79; S, 12.78. Found: C, 72.46; H, 8.75; N, 2.50; S, 12.88.

#### 4. HOMO/LUMO Energies and Band Gaps of pDPP4T-A, pDPP4T-B and pDPP4T-C

**Table S1. Absorption, Onset Redox Potentials, HOMO/LUMO Energies and Band Gaps of pDPP4T-A, pDPP4T-B and pDPP4T-C.**

polymer	$\lambda_{\max}^a$ (nm)		$E_{\text{redl}}^{\text{onset}}$ (V) <sup>c</sup>	$E_{\text{LUMO}}$ (eV) <sup>d</sup>	$E_{\text{oxl}}^{\text{onset}}$ (V) <sup>c</sup>	$E_{\text{HOMO}}$ (eV) <sup>d</sup>	$E_g^{\text{cv}}$ (eV) <sup>e</sup>	$E_g^{\text{opt}}$ (eV) <sup>f</sup>
	( $\epsilon_{\max}$ , M <sup>-1</sup> cm <sup>-1</sup> ) <sup>b</sup>							
	solution	film						
<b>pDPP4T-A</b>	784(80000)	726,784	-1.28	-3.52	0.47	-5.27	1.75	1.33
<b>pDPP4T-B</b>	788(82000)	726,790	-1.26	-3.54	0.46	-5.26	1.71	1.32
<b>pDPP4T-C</b>	800(83000)	726,790	-1.26	-3.54	0.46	-5.26	1.72	1.32

<sup>a</sup> Absorption maxima in CHCl<sub>3</sub> solution (1.0×10<sup>-5</sup> M for each polymer) and the spin-coated thin film; <sup>b</sup> Molar extinction coefficient ( $\epsilon_{\max}$ , M<sup>-1</sup> cm<sup>-1</sup>); <sup>c</sup> Onset potentials (V vs Fc/Fc<sup>+</sup>) for reduction ( $E_{\text{redl}}^{\text{onset}}$ ) and oxidation ( $E_{\text{oxl}}^{\text{onset}}$ ); <sup>d</sup> Estimated with the following equation:  $E_{\text{HOMO}} = - (E_{\text{oxl}}^{\text{onset}} + 4.8)$  eV,  $E_{\text{LUMO}} = - (E_{\text{redl}}^{\text{onset}} + 4.8)$  eV; <sup>e</sup> Based on redox potentials; <sup>f</sup> Based on the absorption spectral data.



**Figure S3.** Normalized UV-vis absorption spectra of **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** in CHCl<sub>3</sub> (1.0×10<sup>-5</sup> M) (A) and their thin films (B).

## 5. Fabrication of FET Devices

Solutions of conjugated polymers were prepared by dissolving the copolymers in chloroform at a concentration of 7.0 mg/mL except **pDPP4T-C** (3.0 mg/mL in 1,1,2,2-tetrachloroethane). The typical polymer film thickness (around 40-45 nm) was measured on profilometer (Ambios Tech. XP-2). Bottom-Gate/Bottom-Contact FETs were fabricated. A heavily doped *n*-type Si wafer and a layer of dry oxidized SiO<sub>2</sub> (300 nm, with roughness lower than 0.1 nm and capacitance of 11 nF cm<sup>-2</sup>) were used as a gate electrode and gate dielectric layer, respectively. The drain-source (*D-S*) gold contacts (28 nm) were fabricated by photo-lithography. The substrates were first cleaned by sonication in acetone and water for 5.0 min and immersed in Piranha solution (2:1 mixture of sulfuric acid and 30% hydrogen peroxide) for 20 min. This was followed by rinsing with deionized water and isopropyl alcohol for several times, and it was blow-dried with nitrogen. Then, the surface was modified with *n*-octadecyltrichlorosilane (OTS). After that, the substrates were cleaned in *n*-hexane, CHCl<sub>3</sub> and isopropyl alcohol. The films of conjugated polymers were fabricated by spin-coating their solutions at 3000 rpm. The annealing process was carried out in vacuum for 1.0 h at each temperature.

The bottom-gate/top-contact devices with fabricated similarly except Au source/drain electrodes (50 nm) were deposited via thermal vacuum evaporation through a shadow mask after spin coating the semiconductor solution and then annealed at different temperatures in vacuum for 1.0 h. Field-effect characteristics of the devices were determined in nitrogen using a Keithley 4200 SCS semiconductor parameter analyzer.

Linear mobility was calculated according to the equation below:

$$I_{DS} = (W/L)C_i\mu(V_{GS} - V_{Th})V_{DS} \quad V_{DS} \ll V_{GS} - V_{Th} \quad (1)$$

The mobility of the OFETs in the saturation region was extracted from the following equation:

$$I_{DS} = \frac{W}{2L}\mu C_i(V_{GS} - V_{Th})^2 \quad (2)$$

Where  $I_{DS}$  is the drain electrode collected current;  $L$  and  $W$  are the channel length and width, respectively;  $\mu$  is the mobility of the device;  $C_i$  is the capacitance per unit area of the gate dielectric layer;  $V_{GS}$  is the gate voltage, and  $V_{Th}$  is the threshold voltage. The  $V_{Th}$  of the device was determined by extrapolating the  $(I_{DS,sat})^{1/2}$  vs.  $V_{GS}$  plot to  $I_{DS} = 0$ .

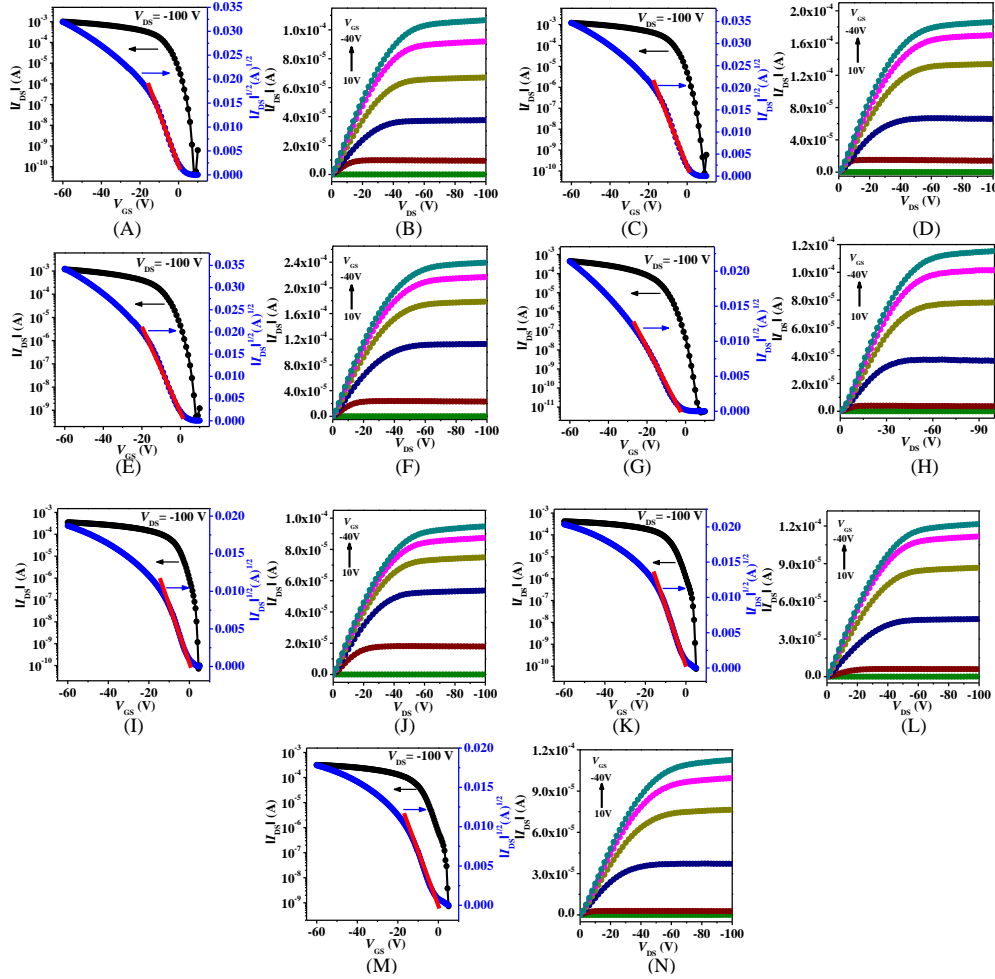
The contact resistance was determined in the following way (a. Luan, S.; Neudeck, G. W. *J. Appl. Phys.* **1992**, 72, 766; b. Lefenfeld, M.; Blanchet, G.; Rogers, J. A. *Adv. Mater.* **2003**, 15, 1188.). For a BGBC FET, the ON resistance,  $R_{ON}$ , in the linear operation regime (source-drain voltage  $\ll$  gate voltage), can be expressed as follows:

$$R_{on} = \frac{\partial V_{DS}}{\partial I_{DS}} \int_{V_{DS} \rightarrow 0}^{V_{GS}} = R_{ch} + R_p = \frac{L}{W\mu_i C_i (V_{GS} - V_{Th})} + R_p \quad (3)$$

where  $R_{ch}$  is the channel resistance,  $R_p$  is the parasitic resistance, and  $V_{GS}$  is the gate voltage. The parasitic resistance,  $R_p$ , which is associated with the contacts between  $S$ - $D$  electrode and semiconductor layer, can be extracted by measuring the ON resistance,  $R_{ON}$ , from the linear region of the FET output characteristics. We got a plot of  $R_{ON}$  as a function of  $L$  at the gate voltage of -30 V, and found that the relationship of  $R_{ON}$  vs  $L$  gives straight lines, indicating that the ON resistance is well expressed by Eq. (3). By extrapolating the relationship of  $R_{ON}$  vs  $L$  to  $L = 0$ , the contact resistance values can be determined. The

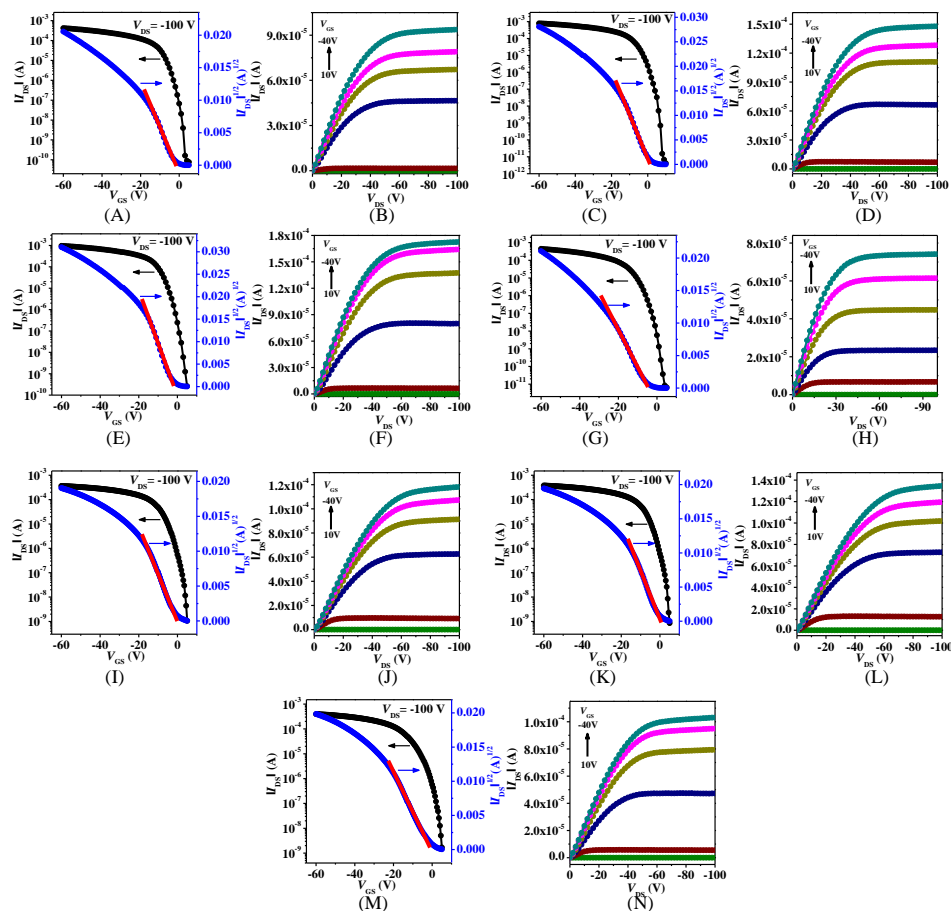
contact resistances for BGBC devices with thin films of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** were determined to be 0.82 M $\Omega$ , 0.21 M $\Omega$ , 0.11 M $\Omega$ , 1.40 M $\Omega$ , 0.71 M $\Omega$ , 0.53 M $\Omega$  and 0.52 M $\Omega$ , respectively.

## 6. Transfer and Output Curves of BGBC and BGTC Devices with Thin Films of pDPP4T-1, pDPP4T-2, pDPP4T-3, pDPP4T, pDPP4T-A, pDPP4T-B and pDPP4T-C



**Figure S4.** The transfer and output curves of BGBC FETs with thin films of **pDPP4T-1** (A, B), **pDPP4T-2** (C, D), **pDPP4T-3** (E, F), **pDPP4T** (G, H), **pDPP4T-A** (I, J), **pDPP4T-B** (K, L) and **pDPP4T-C** (M, N) after thermal annealing at 100 °C; the channel width ( $W$ ) and length ( $L$ ) were 1440  $\mu\text{m}$  and 50  $\mu\text{m}$ , respectively.





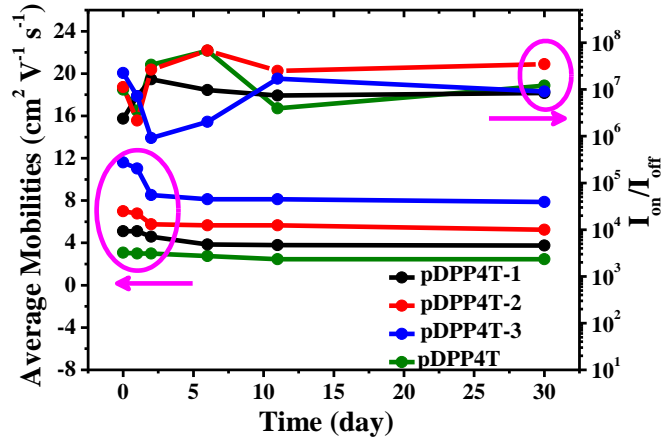
**Figure S5.** The transfer and output curves of BGTC FETs with thin films of **pDPP4T-1** (A, B), **pDPP4T-2** (C, D), **pDPP4T-3** (E, F), **pDPP4T** (G, H), **pDPP4T-A** (I, J), **pDPP4T-B** (K, L) and **pDPP4T-C** (M, N) after thermal annealing at 100 °C; the channel width ( $W$ ) and length ( $L$ ) were 3000  $\mu\text{m}$  and 100  $\mu\text{m}$ , respectively.

**Table S2.** Hole Mobilities ( $\mu_h$ ), Threshold Voltages ( $V_{\text{Th}}$ ) and  $I_{\text{on}}/I_{\text{off}}$  Ratios for BGTC FETs with thin films of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** after Annealing at 100 °C.

polymer	$\mu_h^a / \text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$	$V_{\text{Th, h}}/\text{V}$	$I_{\text{on}}/I_{\text{off}}$
<b>pDPP4T-1</b>	4.8/4.4	-3 - 10	$10^6 - 10^7$
<b>pDPP4T-2</b>	6.4/5.9	0 - 9	$10^7 - 10^8$
<b>pDPP4T-3</b>	8.8/7.1	-5 - 10	$10^6 - 10^7$
<b>pDPP4T-A</b>	3.7/3.1	-5 - 8	$10^5 - 10^6$
<b>pDPP4T-B</b>	4.1/3.5	-4 - 9	$10^5 - 10^6$
<b>pDPP4T-C</b>	2.6/2.1	-3 - 10	$10^5 - 10^6$
<b>pDPP4T</b>	2.6/2.2	-5 - 11	$10^7 - 10^8$

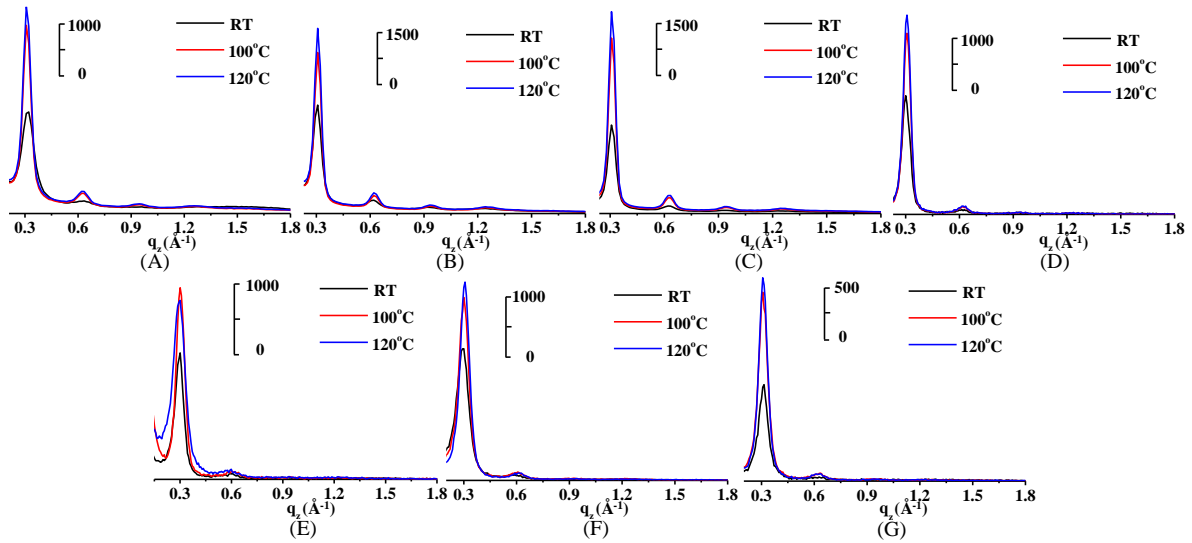
<sup>a</sup> The mobilities were provided in “highest/average” form, and the performance data were obtained based on more than 10 different FETs.

## 7. Devices Stability Data

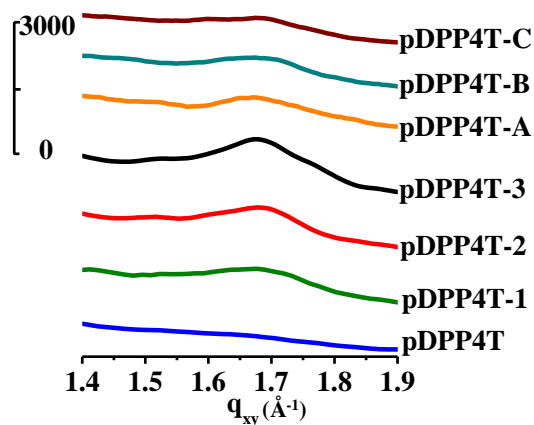


**Figure S6.** Variation of hole mobilities and  $I_{on}/I_{off}$  ratios for BGBC FETs of **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3** and **pDPP4T** after being left in air for 30 days.

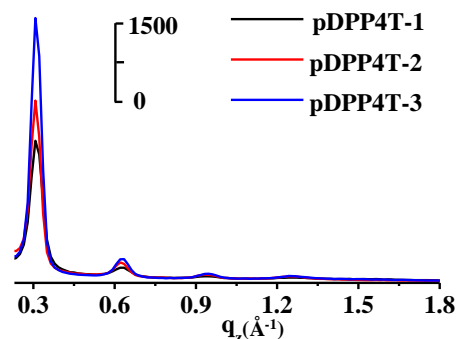
## 8. 1-D GIXRD Patterns



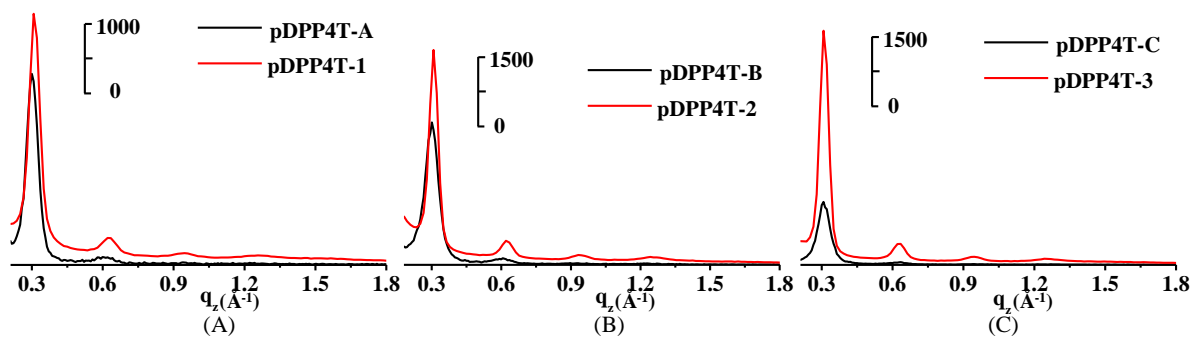
**Figure S7.** 1-D GIXRD patterns in the *out-of-plane* direction for **pDPP4T-1** (A), **pDPP4T-2** (B), **pDPP4T-3** (C), **pDPP4T** (D) and **pDPP4T-A** (E), **pDPP4T-B** (F) and **pDPP4T-C** (G) deposited on OTS-modified SiO<sub>2</sub>/Si substrates after thermal annealing at different temperatures.



**Figure S8.** 1-D GIXRD patterns in the *in-plane* direction for **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T**, **pDPP4T-A**, **pDPP4T-B**, and **pDPP4T-C** deposited on OTS-modified SiO<sub>2</sub>/Si substrates after thermal annealing at 100 °C.

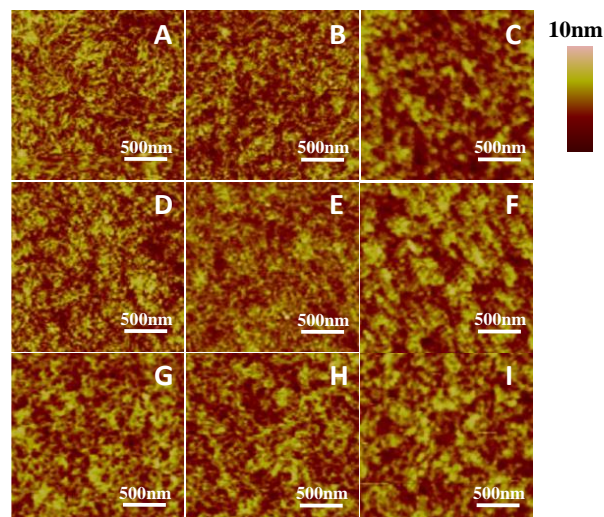


**Figure S9.** 1-D *out-of-plane* X-ray diffraction patterns of **pDPP4T-1**, **pDPP4T-2** and **pDPP4T-3** after thermal annealing at 100 °C.



**Figure S10.** 1-D *out-of-plane* X-ray diffraction patterns of **pDPP4T-1** and **pDPP4T-A** (A), **pDPP4T-2** and **pDPP4T-B** (B) and **pDPP4T-3** and **pDPP4T-C** (C) after thermal annealing at 100 °C.

## 9. AFM Images of pDPP4T-A, pDPP4T-B and pDPP4T-C



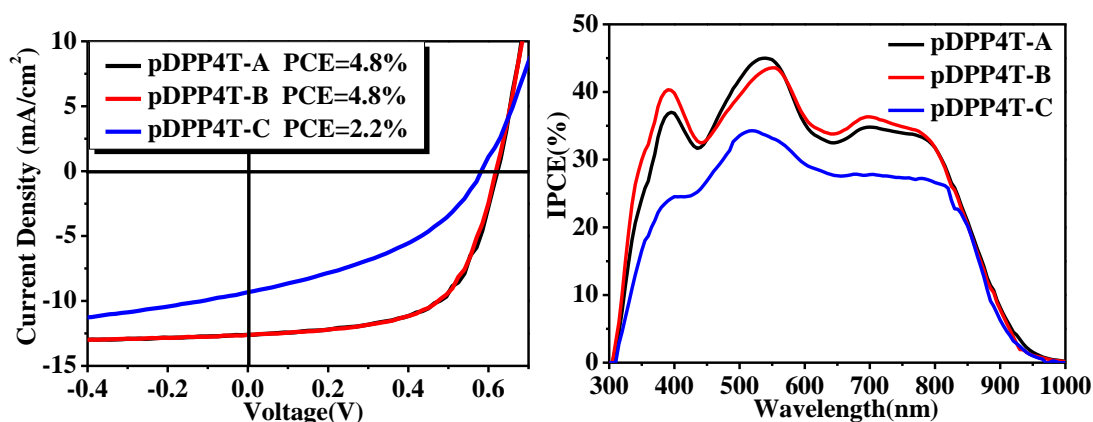
**Figure S11.** AFM height images of thin films of **pDPP4T-A** (A, D, G), **pDPP4T-B** (B, E, H) and **pDPP4T-C** (C, F, I) deposited on OTS-modified SiO<sub>2</sub>/Si substrates at room temperature (*up*) and after thermal annealing at 100 °C (*middle*) and 120 °C (*down*).

## 10. Fabrication of Organic Photovoltaic Cells

OPVs were fabricated with ITO as the positive electrode and Al as the negative electrode. The patterned indium tin oxide (ITO) glass (sheet resistance = 15  $\Omega$ /square) was precleaned in an ultrasonic bath in detergent, deionized water, acetone and isopropyl alcohol, then treated in an ultraviolet-ozone chamber (Jelight Company, USA) for 30 min. A thin layer (30 nm) of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS, Baytron PVP AI 4083, Germany) was spin-coated onto the ITO glass and baked at 150 °C for 15 min. Blend solution were prepared in different solvents at a total concentration of 15-18 mg/ml (donor/acceptor weight ratio:1/2 or 1/1) and stirred 2 hours for complete dissolution. Then, the **pDPP4T**, **pDPP4T-1**, **pDPP4T-2**, **pDPP4T-3**, **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C**/PC<sub>71</sub>BM blend solution was spin-coated. The thickness (ca.

100-120 nm) of the active layer was measured using an Ambios Technology XP-2 profilometer. Ca (ca. 20 nm) and aluminum layer (ca. 70 nm) were then evaporated onto the surface of the active layer under vacuum (ca.  $10^{-5}$  Pa) to form the negative electrode respectively. The active area of the device was  $5.0 \text{ mm}^2$ . The  $J$ - $V$  curves were measured with a computer-controlled Keithley 236 Source Measure Unit. A xenon lamp coupled with AM 1.5 solar spectrum filters was used as the light source, and the optical power at the sample was  $100 \text{ mW cm}^{-2}$ . The incident photon to converted current efficiency (IPCE) spectra were performed at Solar Cell Spectral Response Measurement System QE-R3011 (EnliTechnololy Co. Ltd).

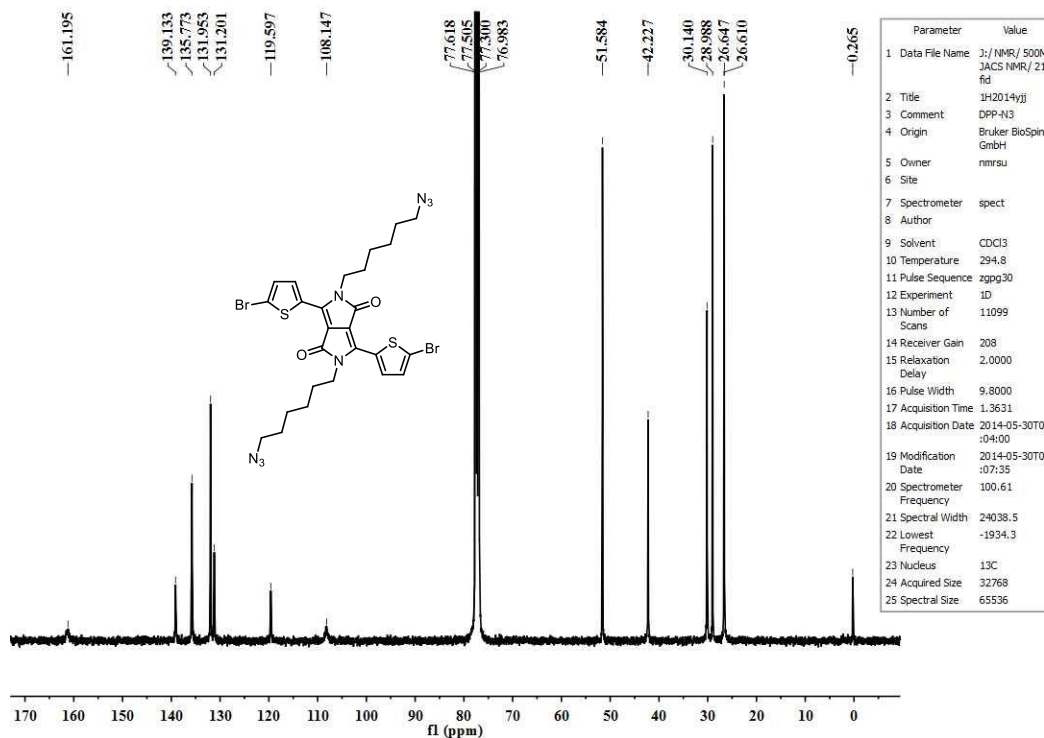
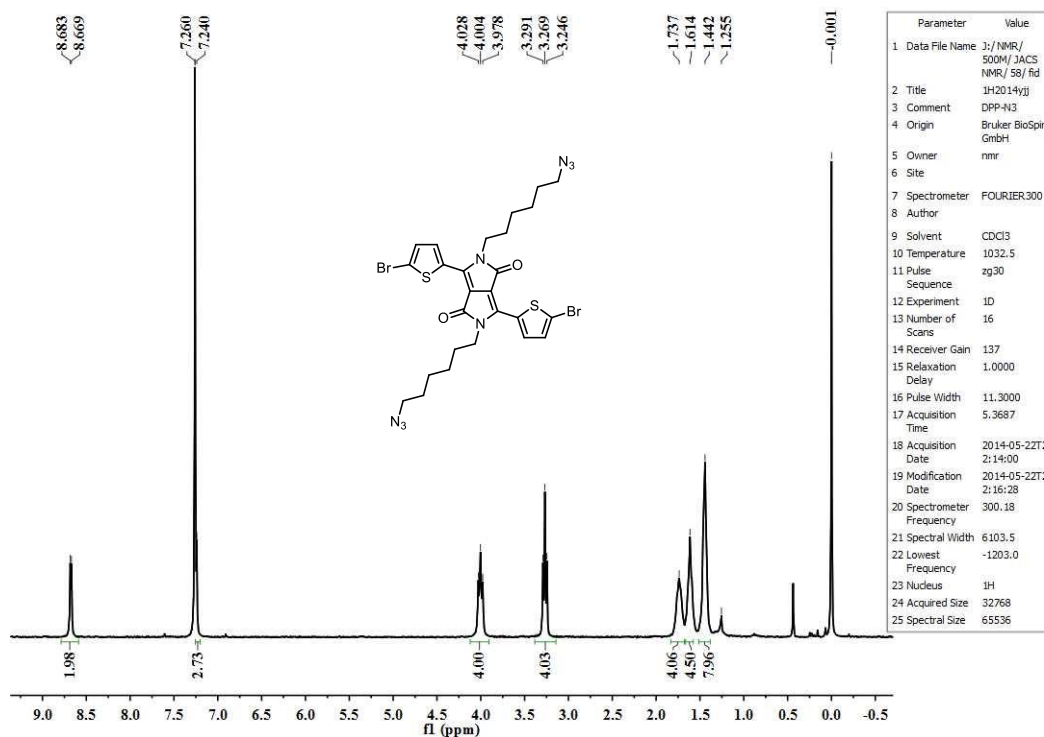
#### 11. $J$ - $V$ Curves and IPCE Spectra of pDPP4T-A, pDPP4T-B and pDPP4T-C with PC<sub>71</sub>BM



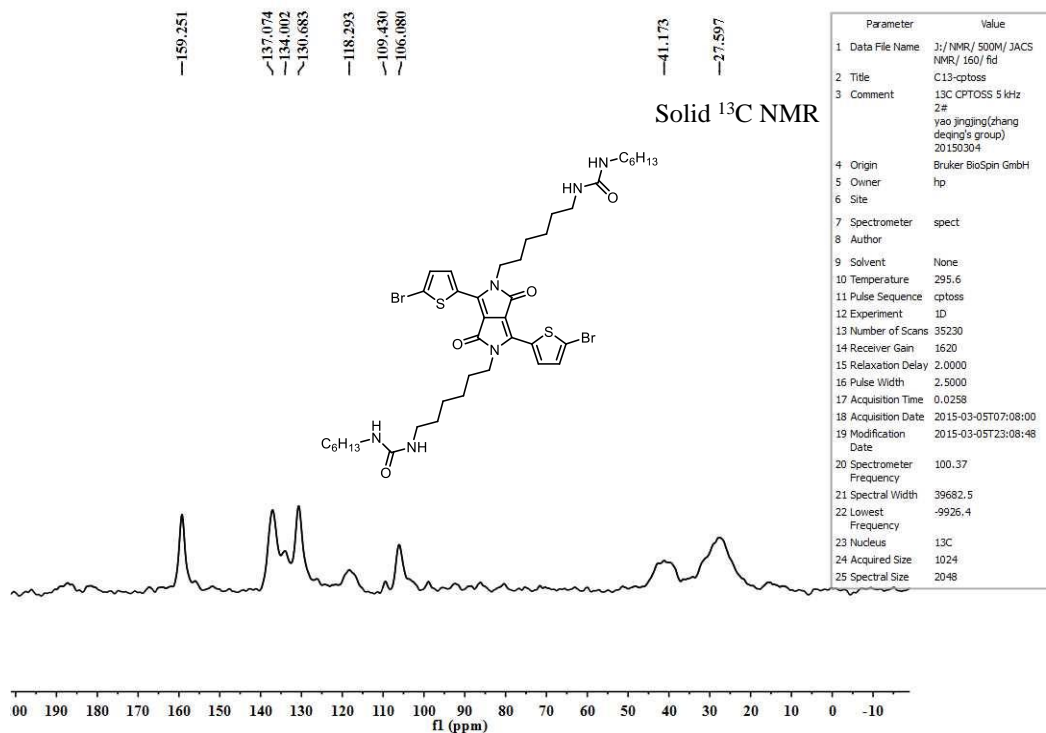
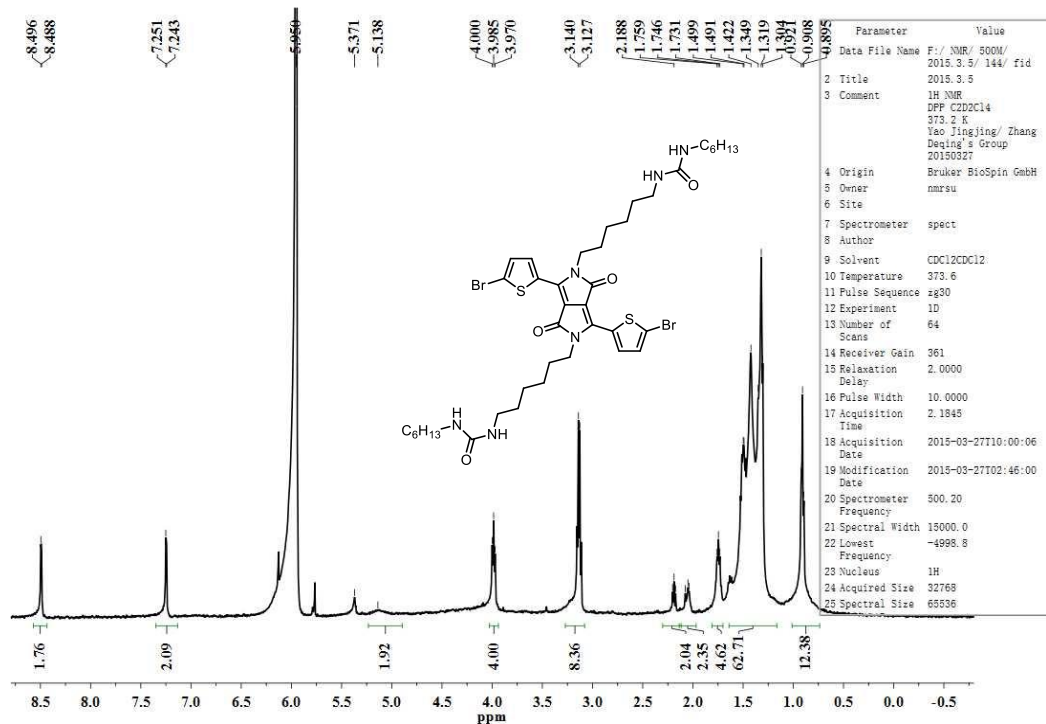
**Figure S12.**  $J$ - $V$  curves (*left*) and IPCE spectra (*right*) of photovoltaic cells with the respective blend films of **pDPP4T-A**, **pDPP4T-B** and **pDPP4T-C** with PC<sub>71</sub>BM at 1:2 weight ratio under AM 1.5 illumination ( $100 \text{ mW/cm}^2$ ).

## 12. <sup>1</sup>HNMR and <sup>13</sup>CNMR Spectra

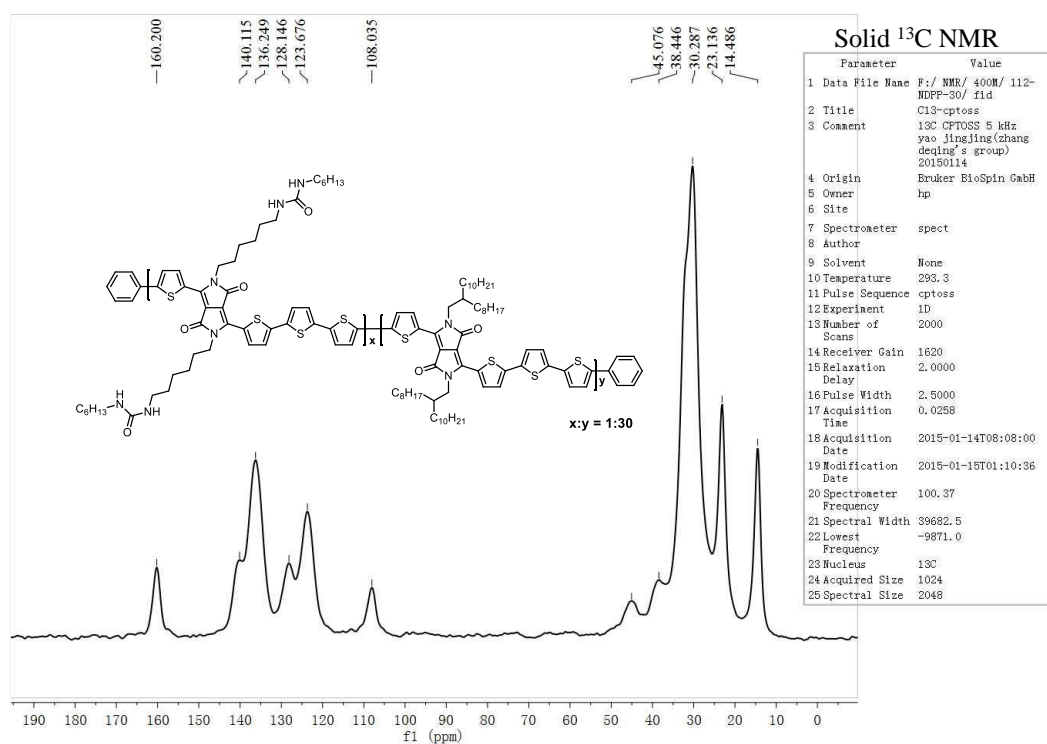
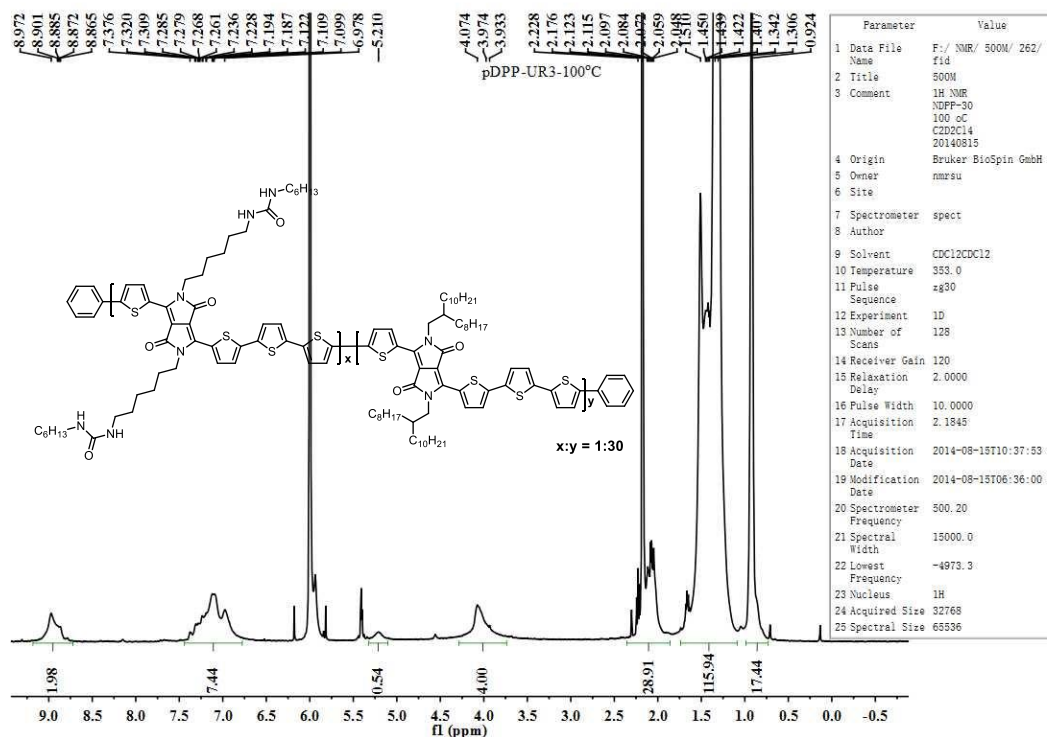
### Compound 5



# Compound 1

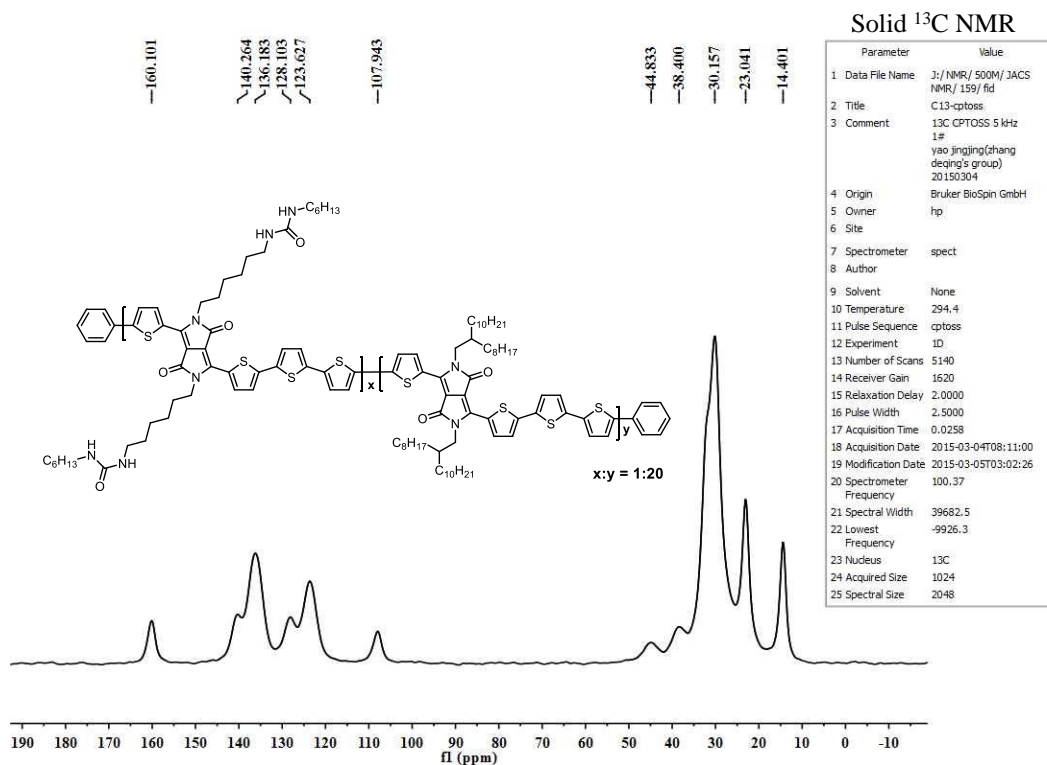
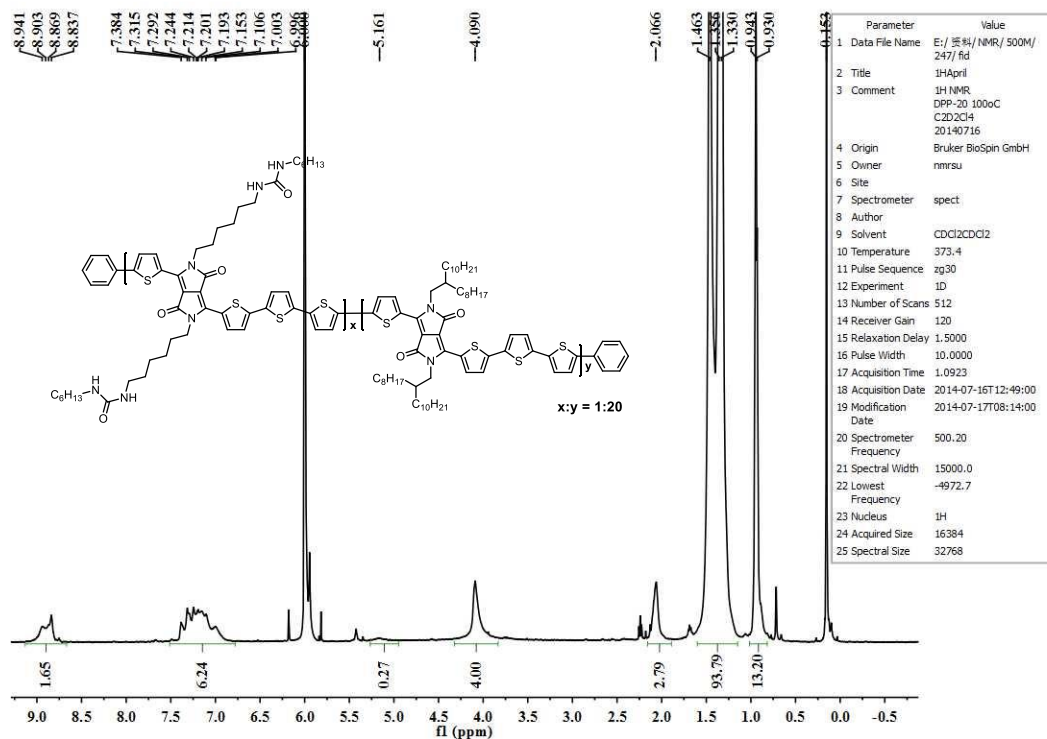


# pDPP4T-1

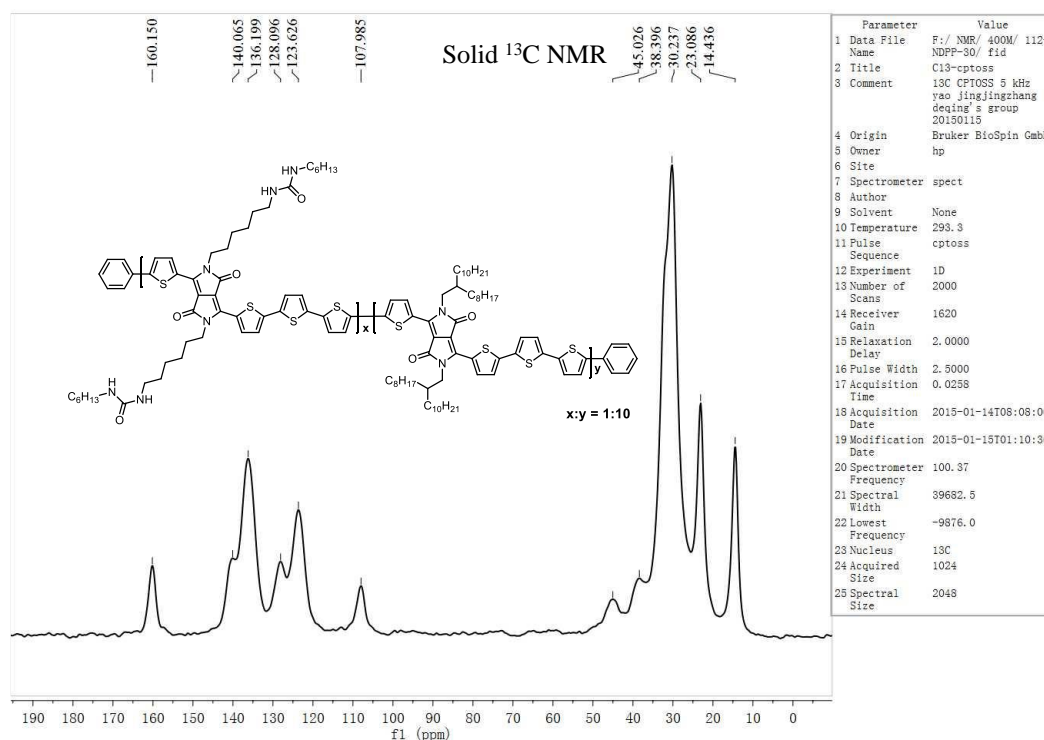
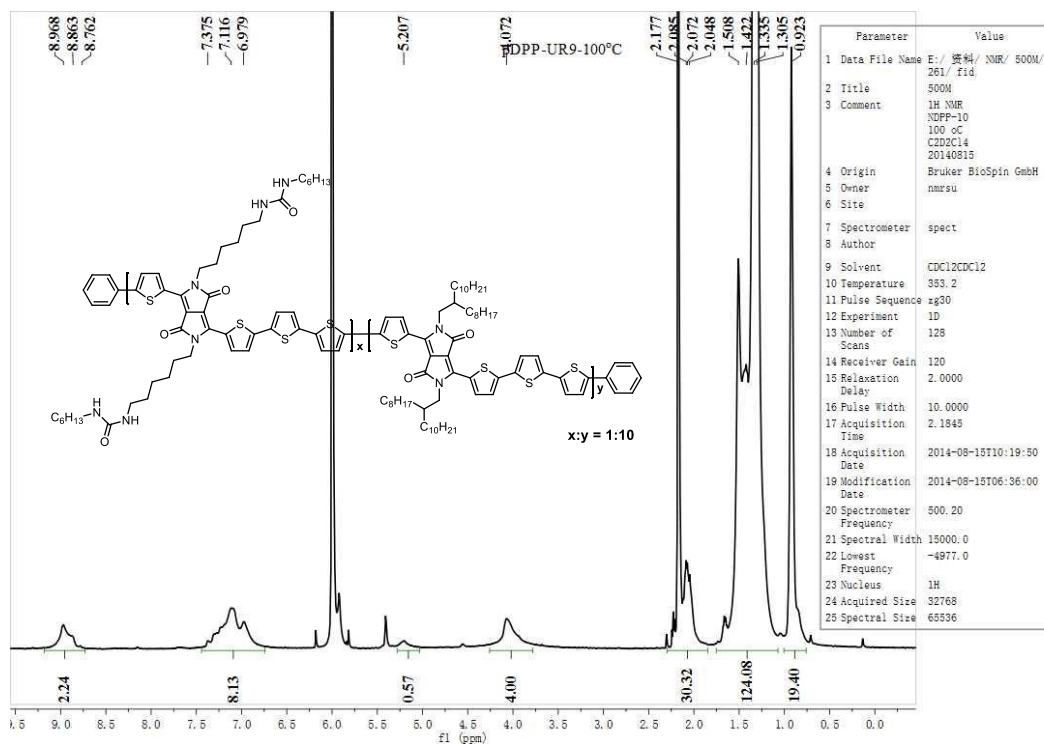




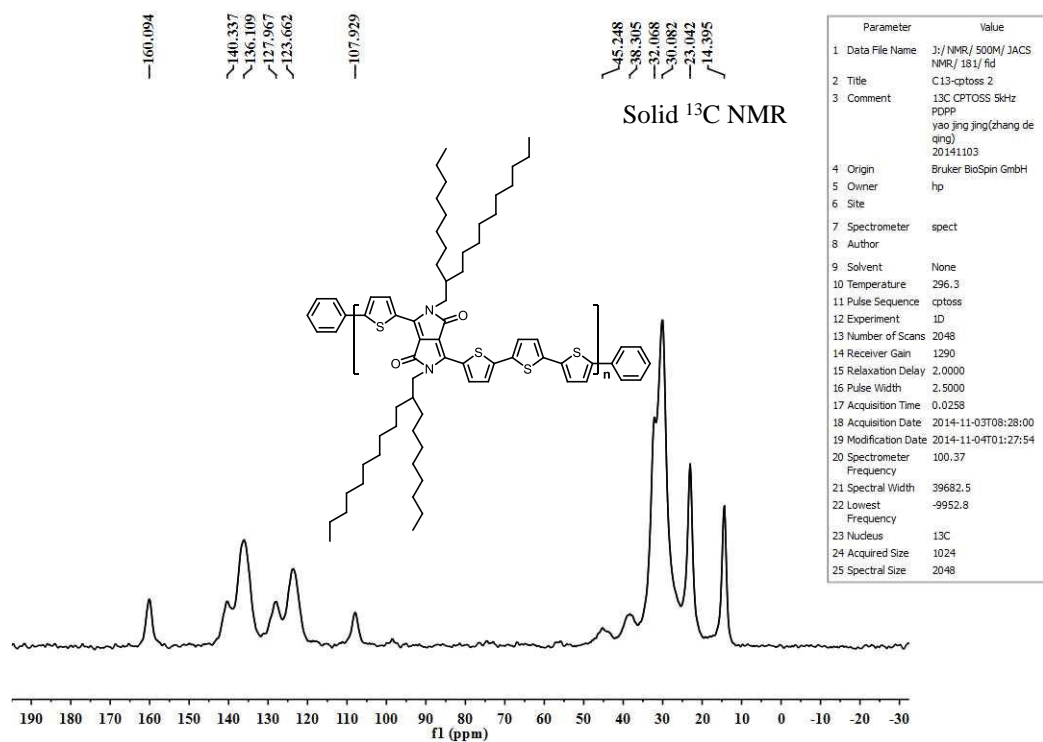
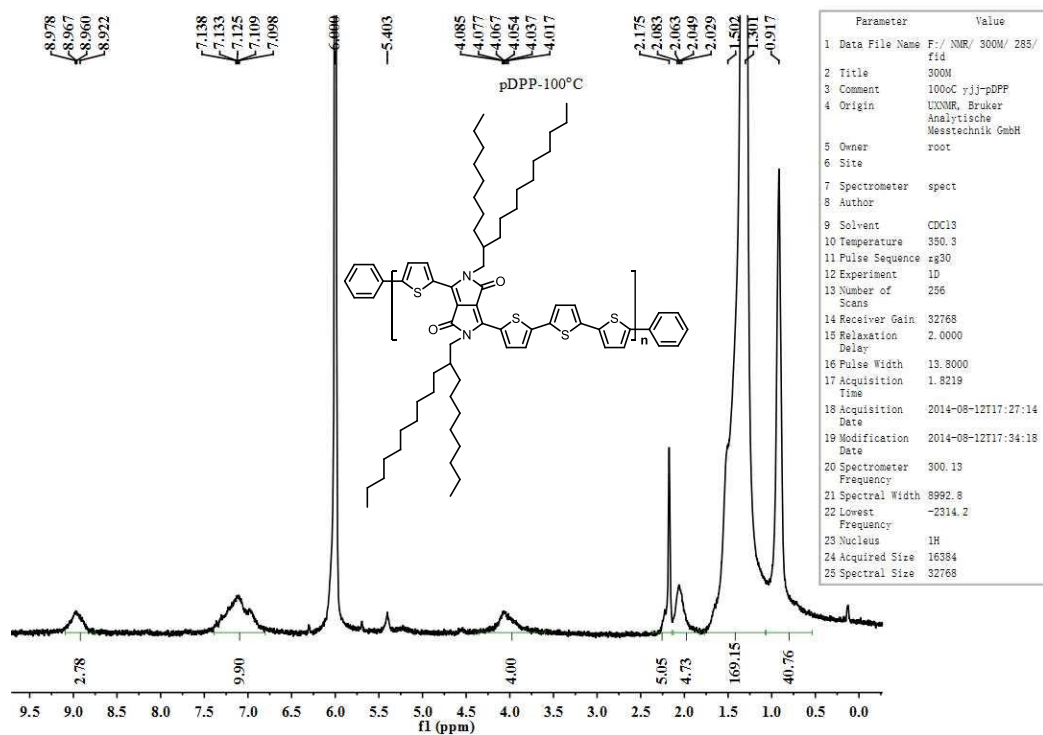
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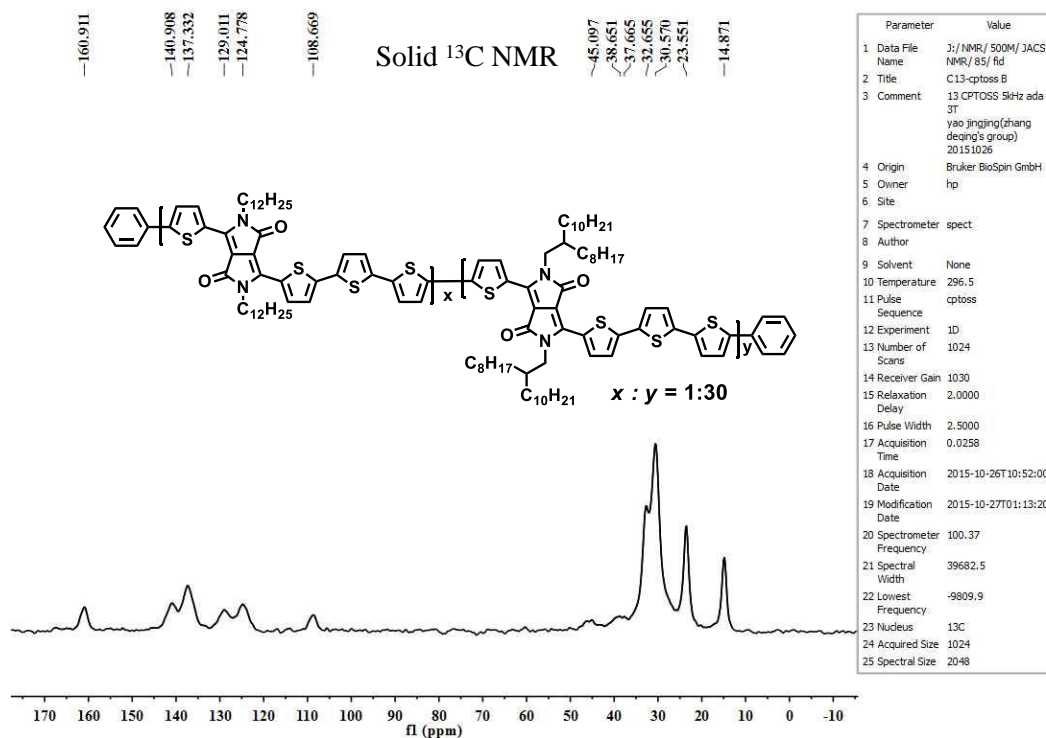
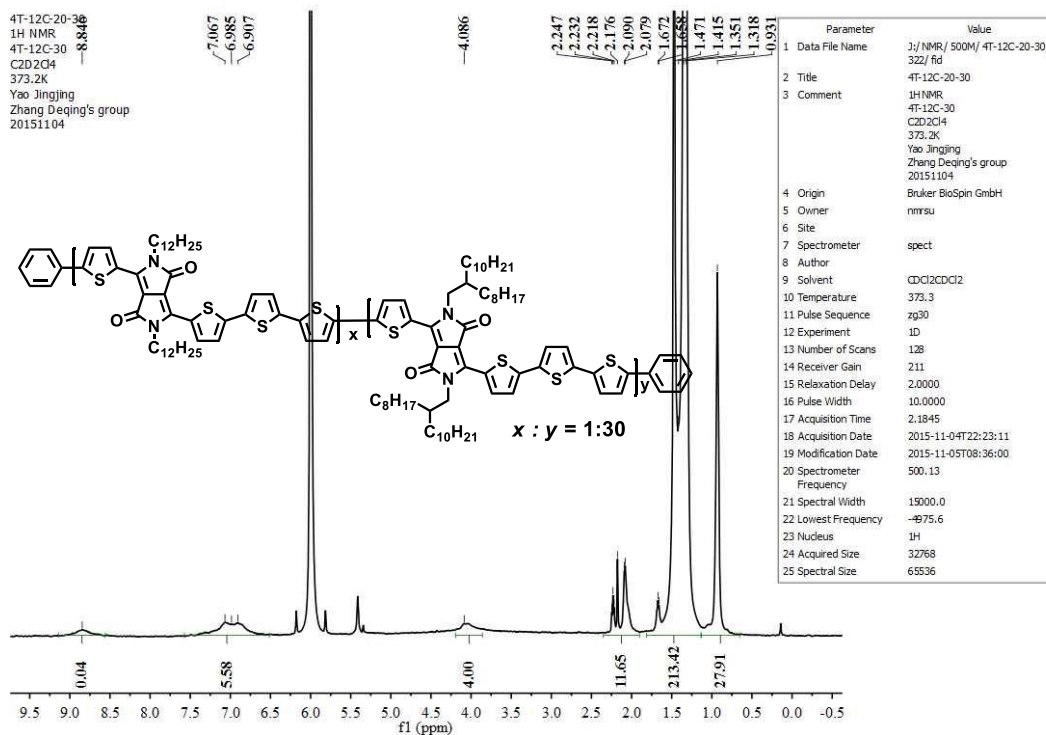
# pDPP4T-3



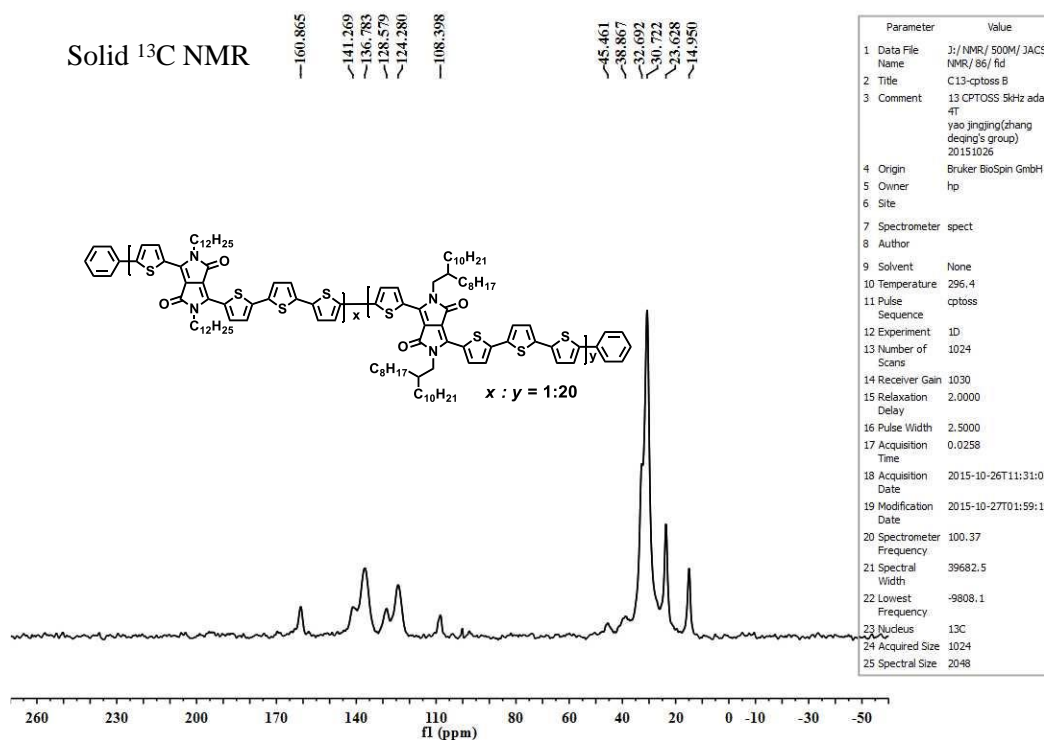
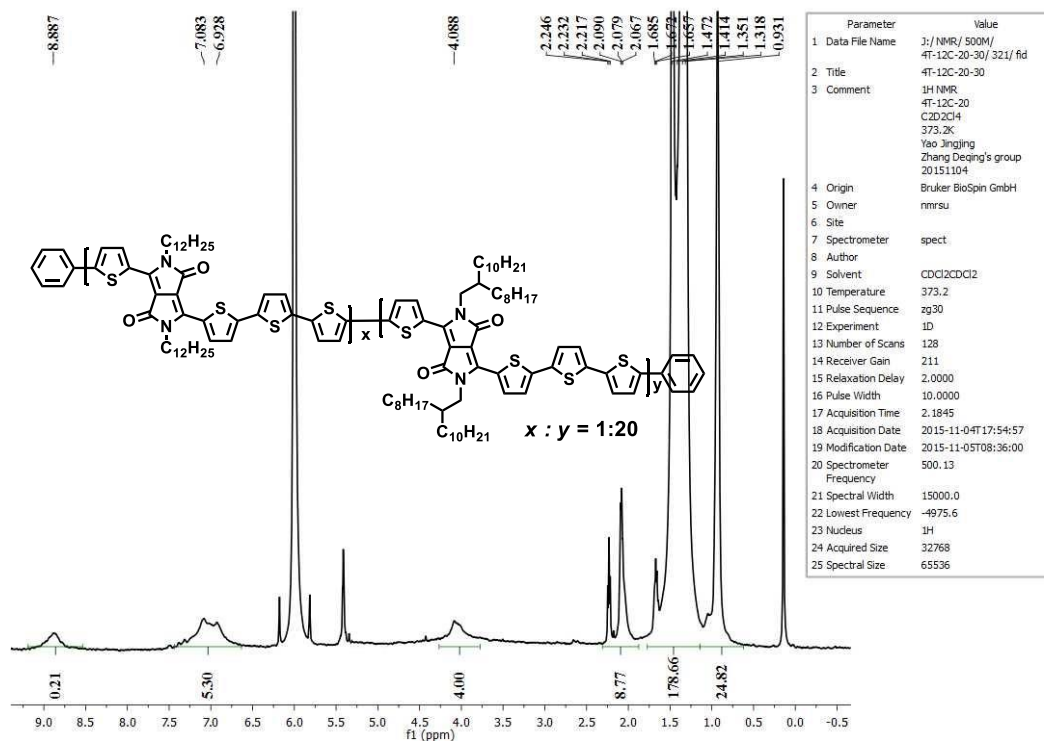
# pDPP4T



# pDPP4T-A



# pDPP4T-B



**pDPP4T-C**

